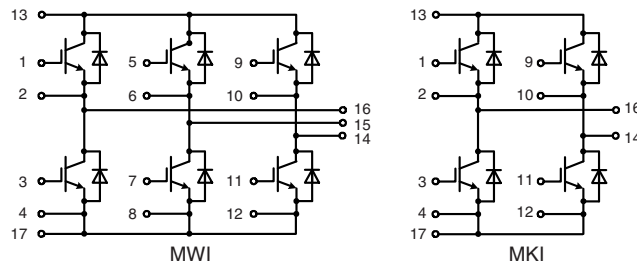


IGBT Modules

Sixpack, H Bridge

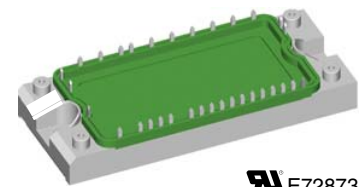
Short Circuit SOA Capability
Square RBSOA



$$I_{C25} = 90 \text{ A}$$

$$V_{CES} = 1200 \text{ V}$$

$$V_{CE(sat) \text{ typ.}} = 1.9 \text{ V}$$



E72873

See outline drawing for pin arrangement

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	90	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	62	A
I_{CM}	$V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$	100	A
V_{CEK}	RBSOA; clamped inductive load; $L = 100 \mu\text{H}$	V_{CES}	
t_{SC}	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$ SCSOA; non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	350	W

Features

- NPT[®] IGBTs
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance also in resonant circuits
- HiPerFRED[™] diode:
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated copper base plate
 - UL registered

Typical Applications

- MWI
 - AC drives
 - power supplies with power factor correction
- MKI
 - motor control
 - . DC motor amature winding
 - . DC motor excitation winding
 - . synchronous motor excitation winding
 - supply of transformer primary winding
 - . power supplies
 - . welding
 - . X-ray
 - . battery charger

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 50 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.9 2.1	2.4 V
$V_{GE(th)}$	$I_C = 2 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.8	0.8 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 50 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega$		80 50 680 30 6.0 4.0	ns ns ns ns mJ mJ
C_{ies}			3.8	nF
Q_{Gon}			350	nC
R_{thJC}				0.35 K/W

IXYS reserves the right to change limits, test conditions and dimensions.

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Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^{\circ}\text{C}$	110	A
I_{F80}	$T_C = 80^{\circ}\text{C}$	70	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 50 \text{ A}$; $V_{GE} = 0 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.2 1.6	2.6 V
I_{RM} t_{rr}	$I_F = 50 \text{ A}$; $di_F/dt = -500 \text{ A}/\mu\text{s}$; $T_{VJ} = 125^\circ\text{C}$ $V_R = 600 \text{ V}$; $V_{GE} = 0 \text{ V}$		40 200	A ns
R_{thJC}	(per diode)			0.61 K/W

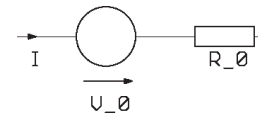
Module

Symbol	Conditions	Maximum Ratings
T_{VJ}	operating	-40...+125 °C
T_{VJM}		-40...+150 °C
T_{stg}		-40...+125 °C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}$; 50/60 Hz	2500 V~
M_d	Mounting torque (M5)	2.7 - 3.3 Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{\text{pin-chip}}$			5	mΩ
d_s	Creepage distance on surface	6		mm
d_A	Strike distance in air	6		mm
R_{thCH}	with heatsink compound		0.02	K/W
Weight			180	g

Equivalent Circuits for Simulation

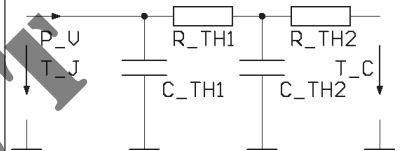
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}$; $T_J = 125^\circ\text{C}$)
 $V_0 = 0.95\text{ V}$; $R_0 = 24\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_o = 1.3 \text{ V}; R_o = 6 \text{ m}\Omega$

Thermal Response



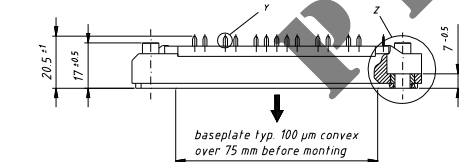
IGBT (typ.)

$$C_{th1} = 0.22 \text{ J/K}; R_{th1} = 0.26 \text{ K/W}$$

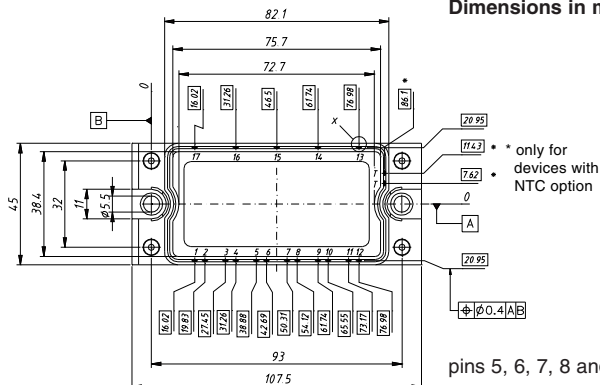
$$C_{th2} = 1.74 \text{ J/K}; R_{th2} = 0.09 \text{ K/W}$$

Free Wheeling Diode (typ.)

$$C_{th1} = 0.151 \text{ J/K}; R_{th1} = 0.483 \text{ K/W}$$

$$C_{th2} = 1.003 \text{ J/K}; R_{th2} = 0.127 \text{ K/W}$$


Dimensions in mm (1 mm = 0.0394")

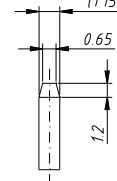


pins 5, 6, 7, 8 and 15 for MWI only

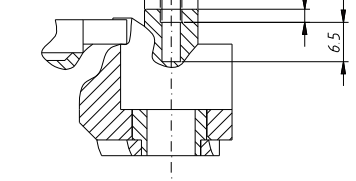
Detail X



Detail Y



Detail Z



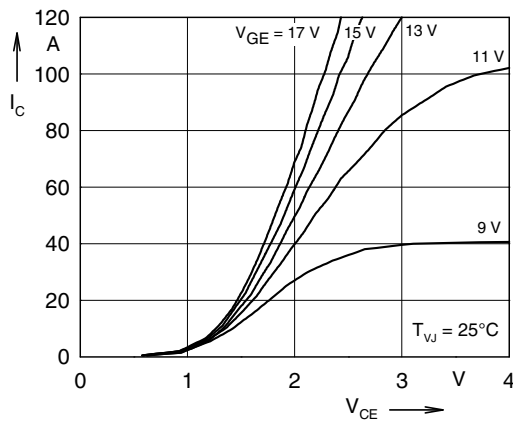


Fig. 1 Typ. output characteristics

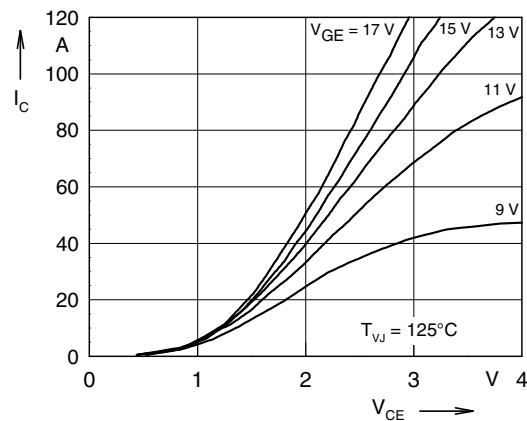


Fig. 2 Typ. output characteristics

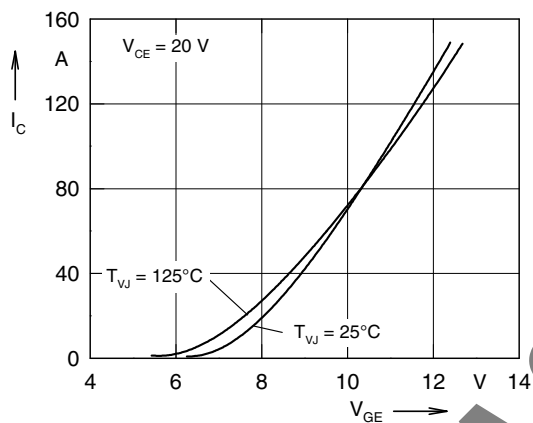


Fig. 3 Typ. transfer characteristics

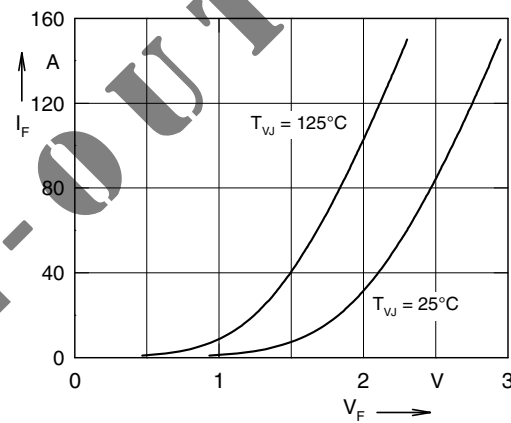


Fig. 4 Typ. forward characteristics of free wheeling diode

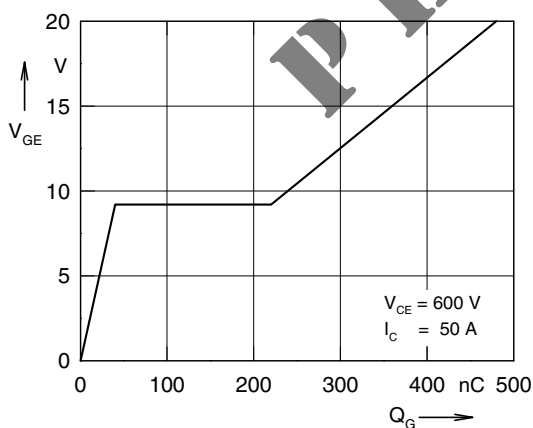


Fig. 5 Typ. turn on gate charge

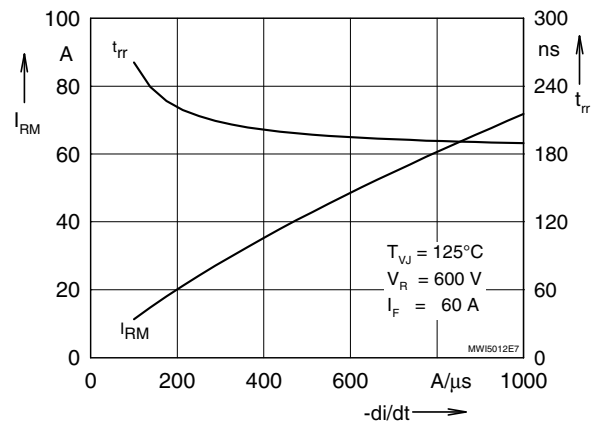


Fig. 6 Typ. turn off characteristics of free wheeling diode

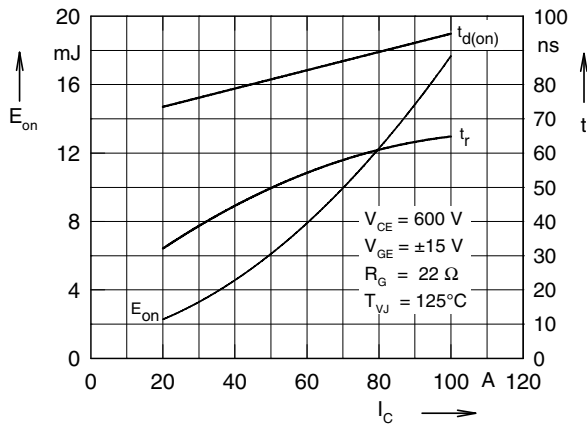


Fig. 7 Typ. turn on energy and switching times versus collector current

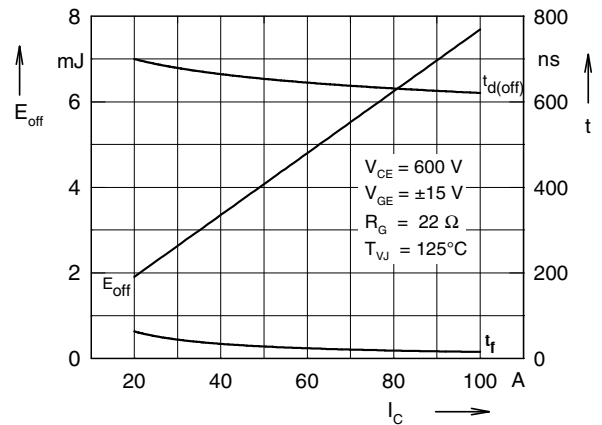


Fig. 8 Typ. turn off energy and switching times versus collector current

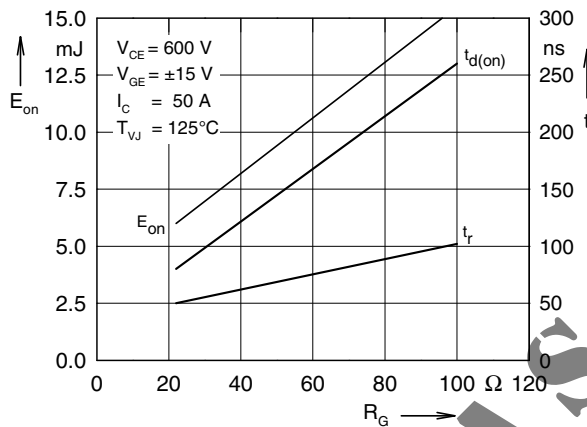


Fig. 9 Typ. turn on energy and switching times versus gate resistor

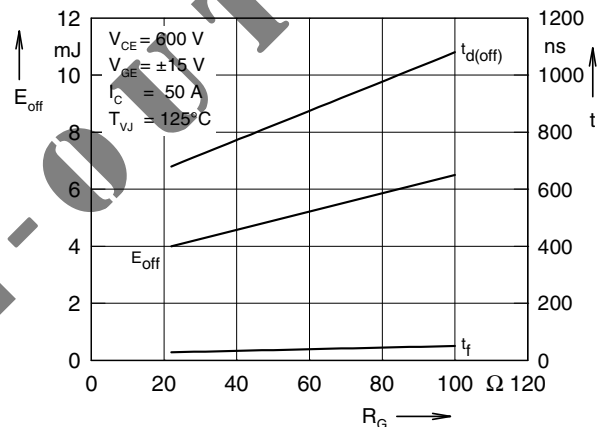


Fig. 10 Typ. turn off energy and switching times versus gate resistor

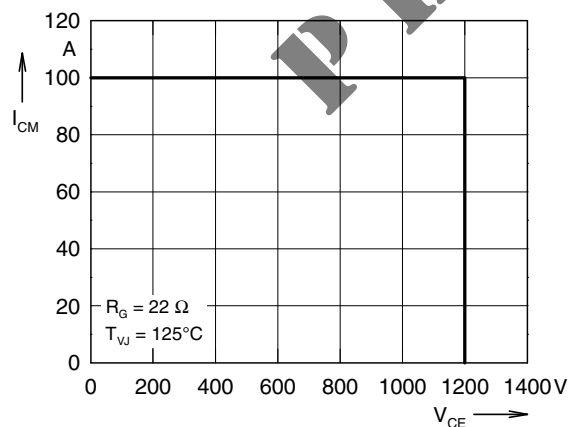


Fig. 11 Reverse biased safe operating area RBSOA

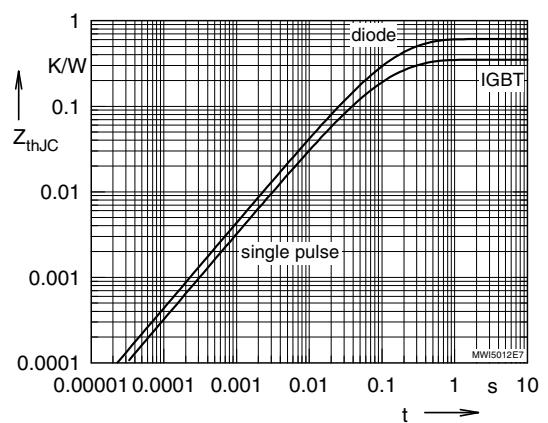


Fig. 12 Typ. transient thermal impedance